# 2SC5121

### Silicon NPN triple diffusion planar type

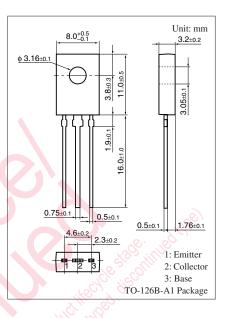
#### For general amplification

#### Features

- High collector-base voltage (Emitter open)  $V_{CBO}$
- High collector-emitter voltage (Base open)  $V_{CEO}$
- $\bullet$  Small collector output capacitance (Common base, input open circuited)  $C_{ob}$
- TO-126B package which requires no insulation plate for installation to the heat sink

Absolute Maximum Ratings $T_a = 25^{\circ}C$							
Symbol	Rating	Unit					
V <sub>CBO</sub>	400	V					
V <sub>CEO</sub>	400	V					
$V_{EBO}$	7	V					
I <sub>C</sub>	70	mA					
I <sub>CP</sub>	100	mA					
P <sub>C</sub>	1.2	W					
Tj	150	°C					
T <sub>stg</sub>	-55 to +150	°C					
	Symbol V <sub>CBO</sub> V <sub>CEO</sub> V <sub>EBO</sub> I <sub>C</sub> P <sub>C</sub> T <sub>j</sub>	Symbol Rating   V <sub>CBO</sub> 400   V <sub>CEO</sub> 400   V <sub>EBO</sub> 7   I <sub>C</sub> 70   I <sub>CP</sub> 100   P <sub>C</sub> 1.2   T <sub>j</sub> 150					

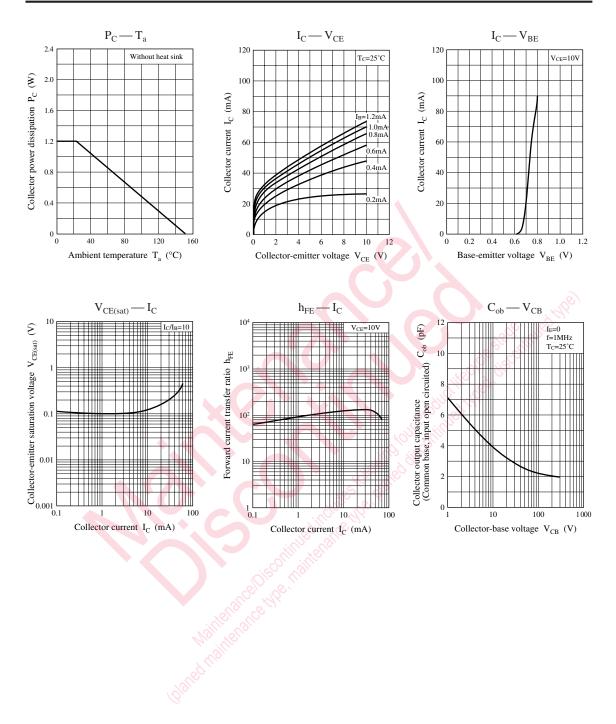
#### Absolute Maximum Ratings $T_a = 25^{\circ}C$



#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 100 \ \mu A, I_{\rm B} = 0$	400			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_{\rm E} = 1 \ \mu A, \ I_{\rm C} = 0$	7			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 300 \text{ V}, I_E = 0$			10	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 380 \text{ V}, I_B = 0, T_a = 80^{\circ}\text{C}$			10	μΑ
Forward current transfer ratio *	h <sub>FE</sub>	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	30		100	
Collector-emitter saturation voltage *	V <sub>CE(sat)</sub>	$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 5 \text{ mA}$			1.2	V
Transition frequency	$f_{T}$	$V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 200 \text{ MHz}$	50	80		MHz
Collector output capacitance	Cob	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		4	8	pF
(Common base, input open circuited)						

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



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